

P-Channel Advanced Power Mosfet

Features

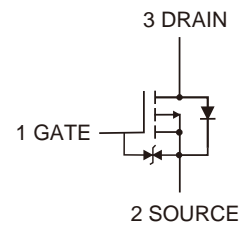
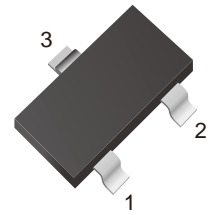
- Low $R_{DS(on)}$ @ $V_{GS} = -4.5V$
- -3.3V Logic Level Control
- P-Channel SOT23 Package
- HMB ESD Protection 4KV
- Lead free in comply with EU RoHS 2011/65/EU directives

Applications

- Load Switch
- Switching circuits
- High-speed line driver
- Power Management Functions

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ Typ | I_D Max |
|---------------|----------------------|-----------|
| -20V | 38m Ω @ -4.5V | -4.8A |
| | 43m Ω @ -3.3V | |



Ordering Information

| Part Number | Marking | Shipping | Reel |
|---------------|---------|--------------------|-----------|
| LTM3415E-TR3 | 3415E | 3000PCS Tape&Reel | 7 inches |
| LTM3415E-TR12 | 3415E | 12000PCS Tape&Reel | 13 inches |

Maximum Ratings and Thermal Characteristics ($T_a = 25^\circ C$ unless otherwise noted)

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

| Symbol | Parameter | Rating | Unit |
|--|-------------------------------------|--------------------|--------------|
| Common Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted) | | | |
| V_{GS} | Gate-Source Voltage | ± 8 | V |
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | -20 | V |
| T_J | Maximum Junction Temperature | 150 | $^\circ C$ |
| T_{STG} | Storage Temperature Range | -50 to 150 | $^\circ C$ |
| Mounted on Large Heat Sink | | | |
| I_{DM} | Pulse Drain Current Tested ① | $T_A = 25^\circ C$ | -30 |
| I_D | Continuous Drain Current | $T_A = 25^\circ C$ | -4.8 |
| | | $T_A = 70^\circ C$ | -3.6 |
| P_D | Maximum Power Dissipation | $T_A = 25^\circ C$ | 1.5 |
| | | $T_A = 70^\circ C$ | 1.0 |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient | 80 | $^\circ C/W$ |

Electrical Characteristics ($T_a=25$ unless otherwise specified)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|---|--|--|------|-------|----------|------------|
| Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated) | | | | | | |
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=-250\mu A$ | -20 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current($T_A=25^\circ\text{C}$) | $V_{DS}=-20V, V_{GS}=0V$ | | | -1 | μA |
| | Zero Gate Voltage Drain Current($T_A=125^\circ\text{C}$) | $V_{DS}=-16V, V_{GS}=0V$ | | | -100 | μA |
| I_{GSS} | Gate-Body Leakage Current | $V_{GS}=\pm 8V, V_{DS}=0V$ | | | ± 10 | μA |
| $V_{GS(TH)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=-250\mu A$ | -0.4 | -0.7 | -1.2 | V |
| $R_{DS(ON)}$ | Drain-Source On-State Resistance② | $V_{GS}=-4.5V, I_D=-4A$ | | 38 | 45 | m Ω |
| $R_{DS(ON)}$ | Drain-Source On-State Resistance② | $V_{GS}=-3.3V, I_D=-3A$ | | 43 | 55 | m Ω |
| $R_{DS(ON)}$ | Drain-Source On-State Resistance② | $V_{GS}=-2.5V, I_D=-2A$ | | 52 | 65 | m Ω |
| Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated) | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS}=-10V, V_{GS}=0V,$ $f=1\text{MHz}$ | | 675 | | pF |
| C_{oss} | Output Capacitance | | | 120 | | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 85 | | pF |
| Q_g | Total Gate Charge | $V_{DS}=-10V$ $I_D=-4A,$ $V_{GS}=-4.5V$ | | 14.2 | | nC |
| Q_{gs} | Gate Source Charge | | | 3.2 | | nC |
| Q_{gd} | Gate Drain Charge | | | 5.8 | | nC |
| Switching Characteristics | | | | | | |
| $t_{d(on)}$ | Turn on Delay Time | $V_{DD}=-10V,$ $I_D=-2A,$ $R_G=3.3\Omega,$ $V_{GS}=-4.5V$ | | 15 | | ns |
| t_r | Turn on Rise Time | | | 11 | | ns |
| $t_{d(off)}$ | Turn Off Delay Time | | | 22 | | ns |
| t_f | Turn Off Fall Time | | | 35 | | ns |
| Source Drain Diode Characteristics | | | | | | |
| I_{SD} | Source drain current(Body Diode) | $T_A=25^\circ\text{C}$ | | | -2 | A |
| V_{SD} | Forward on voltage ② | $T_J=25^\circ\text{C}, I_{SD}=-2A,$ $V_{GS}=0V$ | | -0.83 | -1.2 | V |

Notes:

- ① Pulse width limited by maximum allowable junction temperature
 ② Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.



Characteristic Curves

Fig1. Typical Output Characteristics

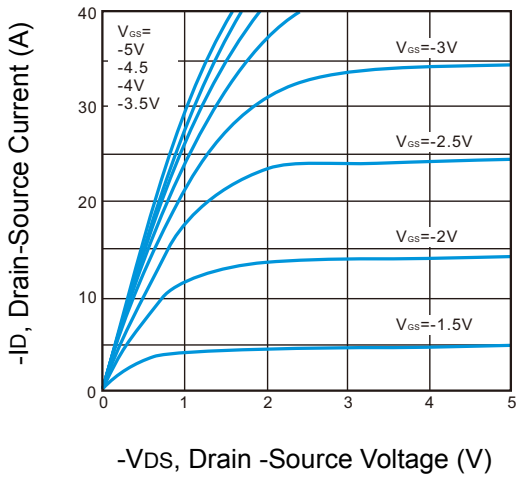


Fig2. Normalized Threshold Voltage Vs Temperature

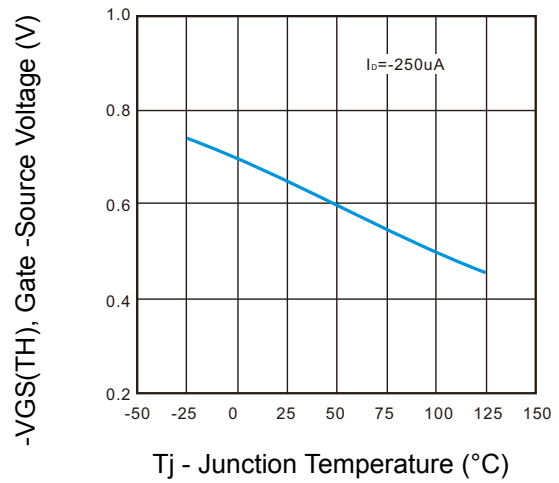


Fig3. Typical Transfer Characteristics

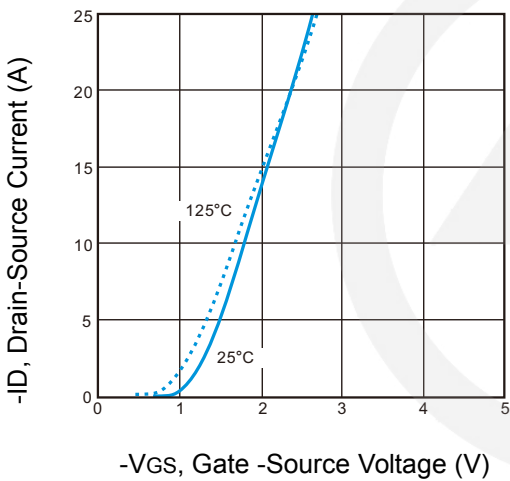


Fig4. Drain -Source Voltage vs Gate -Source Voltage

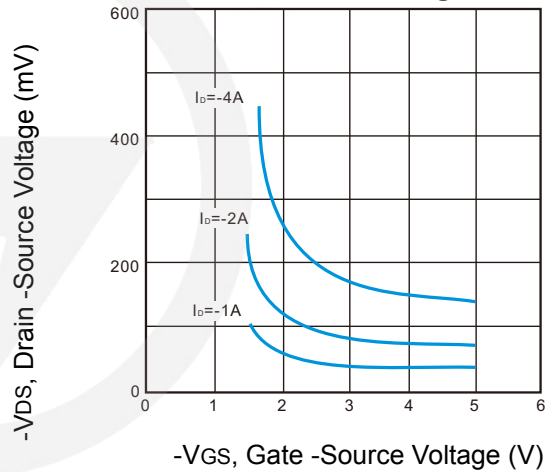


Fig5. Typical Source-Drain Diode Forward Voltage

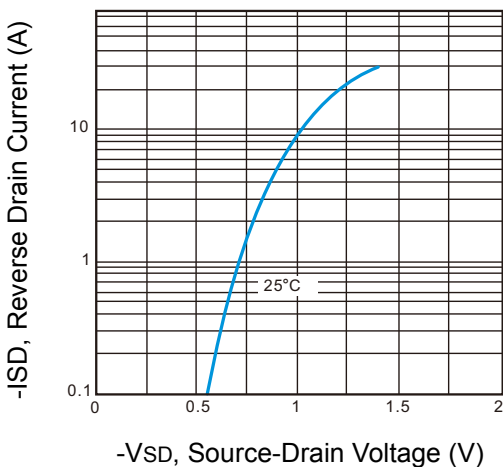
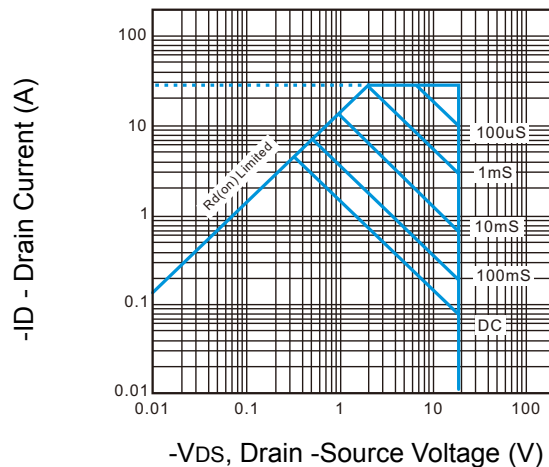


Fig6. Maximum Safe Operating Area



Characteristic Curves

Fig7. Typical Capacitance Vs Drain-Source Voltage

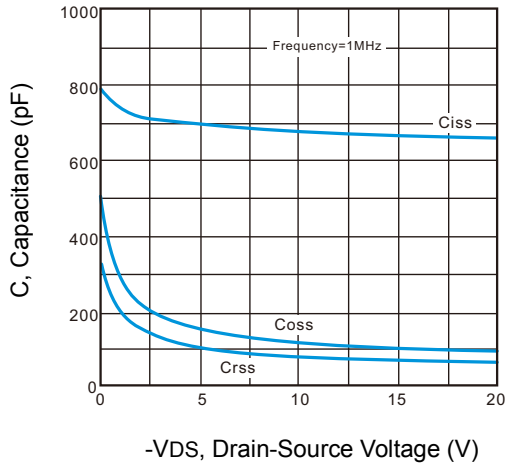


Fig8. Typical Gate Charge Vs Gate-Source Voltage

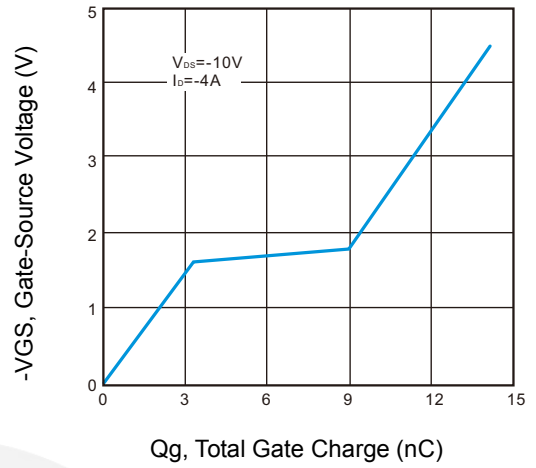


Fig9. Normalized Maximum Transient Thermal Impedance

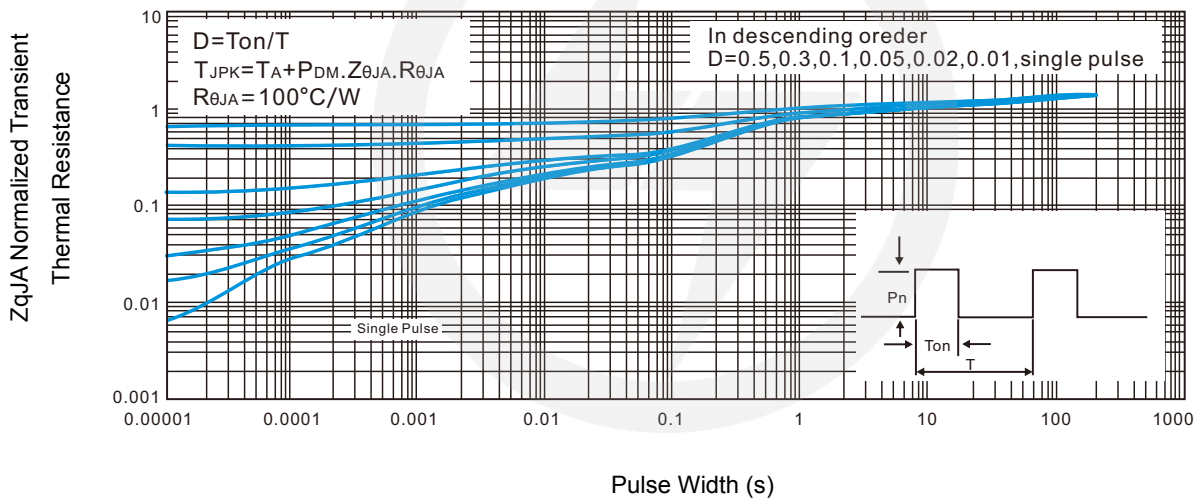
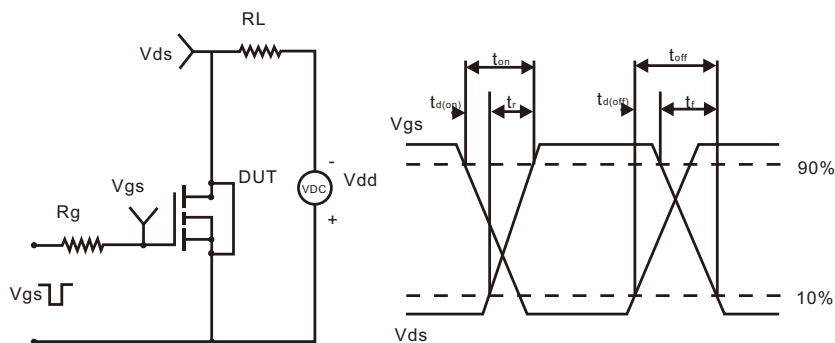
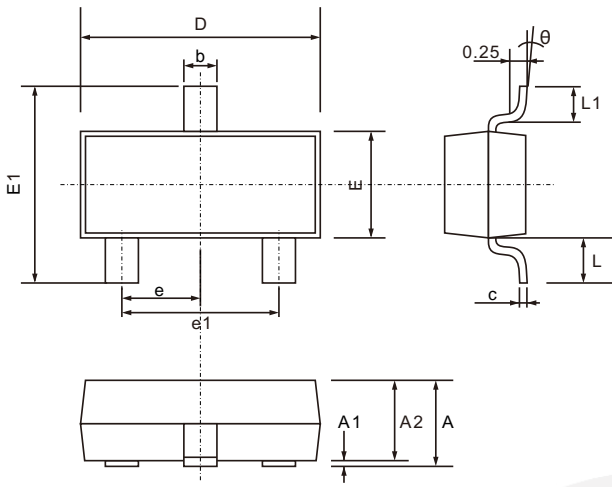


Fig10. Switching Time Test Circuit and waveforms



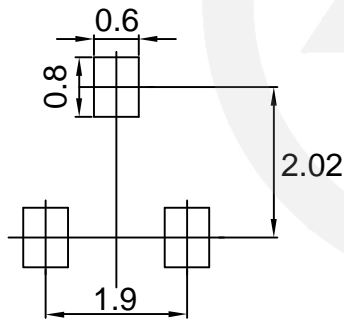
SOT-23 Package Outline

Unit: mm

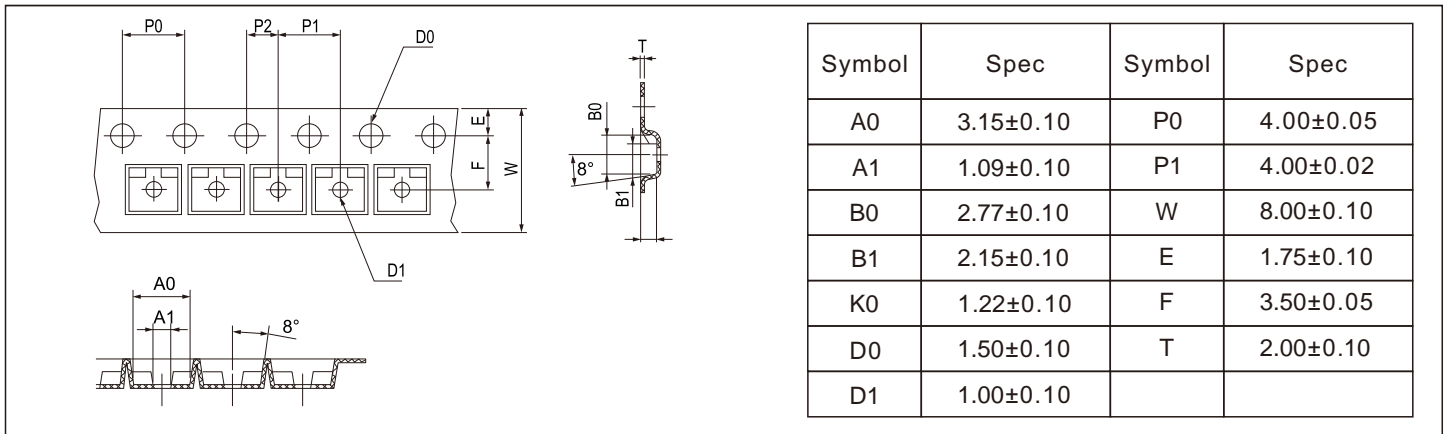
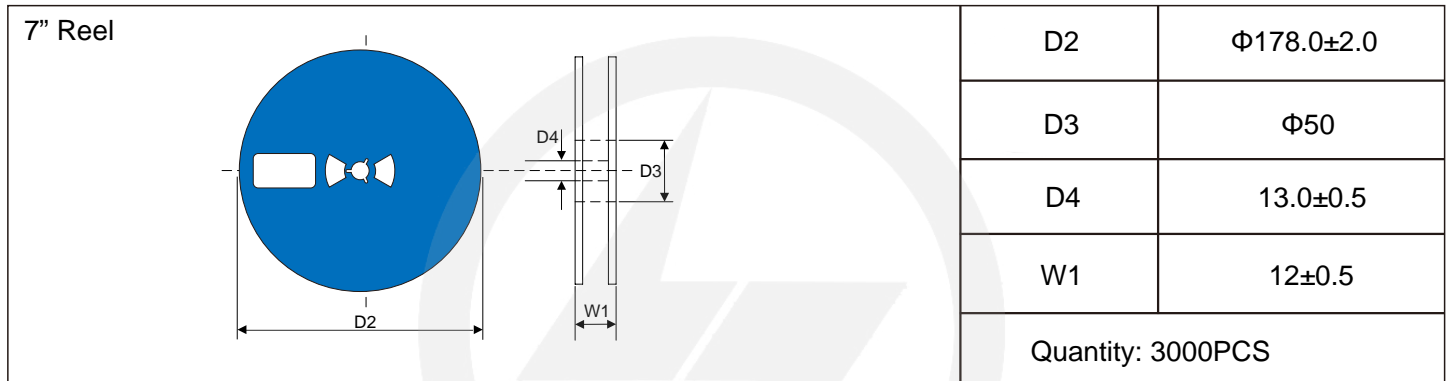
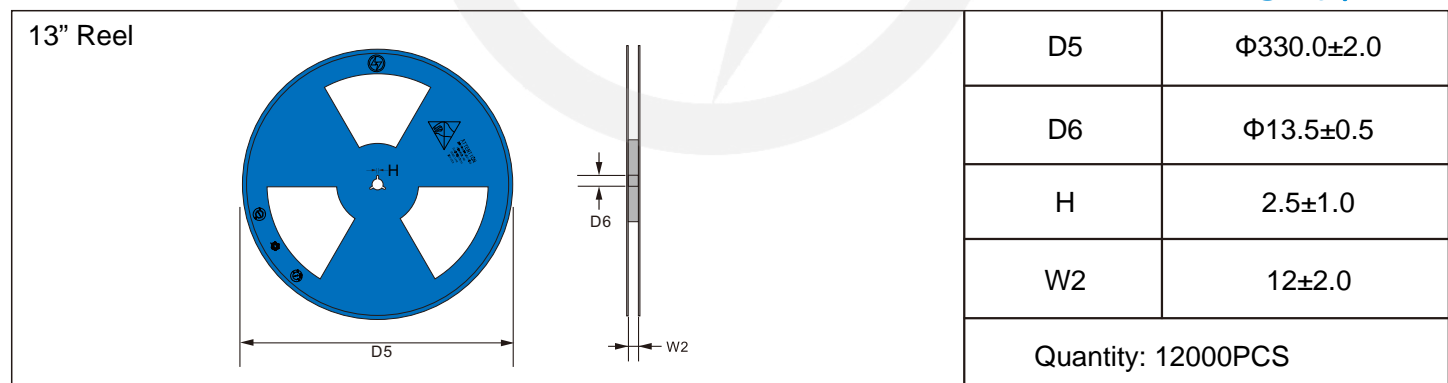
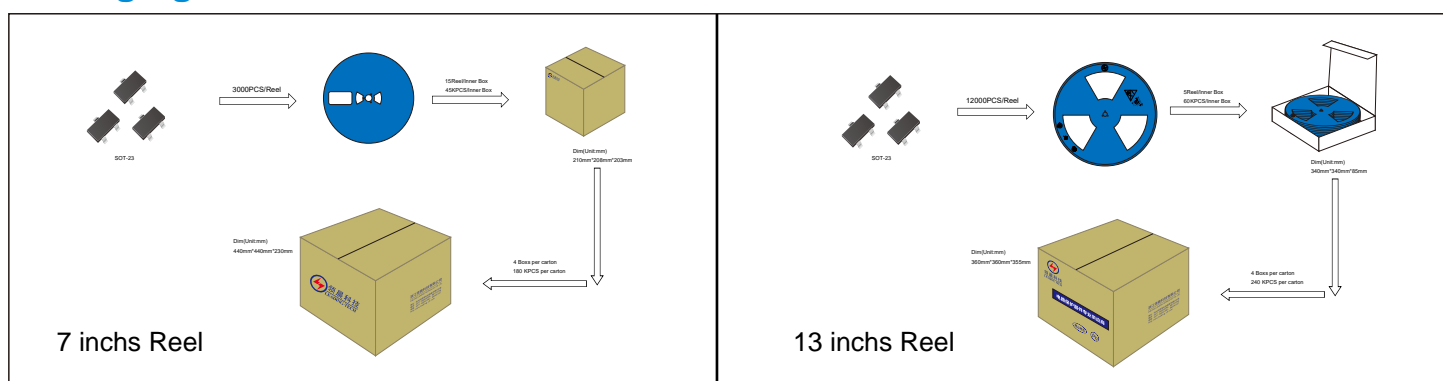


| SYMBOL | DIMENSIONS | |
|--------|------------|-------|
| | MIN. | MAX. |
| A | 0.900 | 1.200 |
| A1 | 0.000 | 0.100 |
| A2 | 0.900 | 1.050 |
| b | 0.300 | 0.500 |
| c | 0.080 | 0.200 |
| D | 2.700 | 3.100 |
| E | 1.200 | 1.400 |
| E1 | 2.200 | 2.600 |
| e | 0.950 TYP. | |
| e1 | 1.750 | 2.050 |
| L | 0.550 TYP. | |
| L1 | 0.300 | 0.500 |
| θ | 0° | 8° |

SOT-23 Suggested Pad Layout

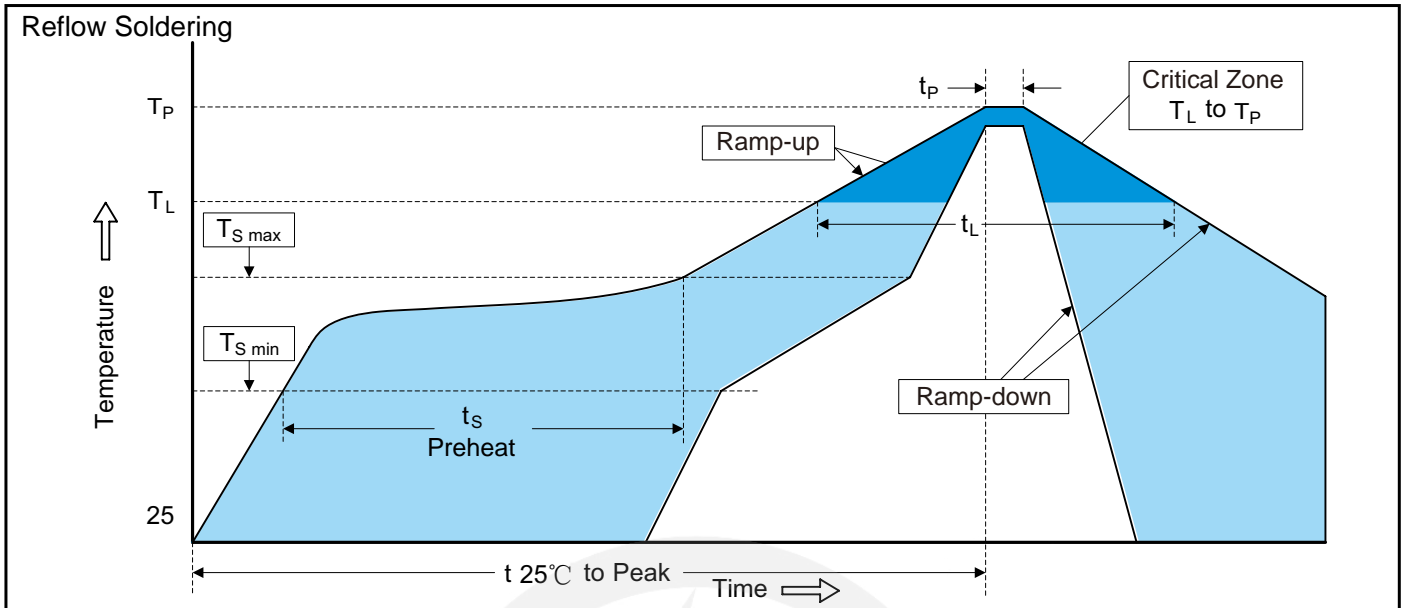


Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$
 3. The pad layout is for reference purpose only.

Carrier Tape Dimensions
Unit : mm

Reel Dimensions
Unit : mm

Reel Dimensions
Unit : mm

Packaging




Recommended Soldering Conditions



Recommended Conditions

| Profile Feature | Pb-Free Assembly |
|--|------------------|
| Average ramp-up rate (T _L to T _P) | 3°C/second max. |
| Preheat | |
| -Temperature Min (T _{S min}) | 150°C |
| -Temperature Max (T _{S max}) | 200°C |
| -Time (min to max) (t _s) | 60-180 seconds |
| T _{S max} to T _L | |
| -Ramp-up Rate | 3°C/second max. |
| Time maintained above: | |
| -Temperature (T _L) | 217°C |
| -Time (t _L) | 60-150 seconds |
| Peak Temperature (T _P) | 260°C |
| Time within 5°C of actual Peak Temperature (t _p) | 20-40 seconds |
| Ramp-down Rate | 6°C/second max. |
| Time 25°C to Peak Temperature | 8 minutes max. |

Important Notice and Disclaimer

Leading-Tech reverses the right to make changes to this document and its products and specifications at any time without notice.

Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

Leading-Tech makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, not does Leading-Tech assume any liability for application assistance or customer product design.

Leading-Tech does not warrant or accept any liability with products which are purchase or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of Leading-Tech.

Leading-Tech products are not authorized for use as critical components in life support devices or systems without express written approval of Leading-Tech.

Version Update Information

| Series NO. | Enactment/Revision Date | Effective Date | Version | Revision Content | Revision Reason | Revision Person | Note |
|------------|-------------------------|----------------|---------|-------------------------------|-----------------|-----------------|------|
| 01 | 2024.03.20 | 2024.03.20 | 3.0 | New file | / | Ding | |
| 02 | 2025.06.16 | 2025.06.16 | 3.1 | Update packaging information | / | Ding | |
| 03 | 2026.03.05 | 2026.03.05 | 3.2 | Package outline E1(max)=2.6mm | / | Ding | |